

IntelliMAX™ 28 V, Over-Voltage, Over-Current Protection Load Switch with Adjustable Current-Limit Control

FPF2595

Description

The FPF2595 advanced load—management switch targets applications requiring a highly integrated solution. It disconnects loads powered from the DC power rail (<6 V) with stringent off—state current targets and high load capacitances (<100 μF). The FPF2595 consists of a slew—rate controlled low—impedance MOSFET switch (35 m Ω typical) and integrated analog features. The slew—rate controlled turn—on characteristic prevents inrush current and the resulting excessive voltage droop on power rails. FPF2595 has over—voltage protection and over— temperature protection.

The FPF2595 has a True Reverse–Current Blocking (TRCB) function that obstructs unwanted reverse current from V_{OUT} to V_{IN} during ON and OFF states. The exceptionally low off–state current drain (<2 μA maximum) facilitates compliance with standby power requirements. The input voltage range operates from 2.5 V to 5.5 VDC to support a wide range of applications in consumer, optical, medical, storage, portable, and industrial–device power management. Switch control is managed by a logic input (active HIGH) capable of interfacing directly with low–voltage control signal / General–Purpose Input / Output (GPIO) without an external pull–down resistor.

The device is packaged in advanced, fully "green" compliant, 1.3 mm x 1.8 mm, Wafer–Level Chip–Scale Packages (WLCSP).

Features

- V_{IN}: 2.5 V~5.5 V
- 28 V Absolute Ratings at V_{OUT}
- Current Capability: 3.9 A
 - ◆ Typ 0.1 A~3.5 A with 10% Accuracy
- $\bullet~$ $R_{ON}\!\!:$ Typ. 35 m Ω & Max. 50 m Ω at 5 V_{IN} and 1 A I_{OUT}
- Output OVP: Min. = 5.6 V, Typ. = 5.8 V, Max. = 6 V
- No Output Discharge During Off State
- Open-Drain OCP on FLAGB
- Thermal Shutdown
- Under-Voltage Lockout (UVLO)
- True Reverse-Current Blocking (TRCB)
- Logic CMOS IO Meets JESD76 Standard for GPIO Interface and Related Power Supply Requirements



WLCSP12 1.3x1.8x0.495 CASE 567RA

MARKING DIAGRAM

TY&K &.&2&Z

TY = Device Code

&K = 2-Digits Lot Run Traceability Code

&. = Pin One Dot&2 = 2-Digit Date Code

&Z = Assembly Plant Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 8 of this data sheet.

Features (continued)

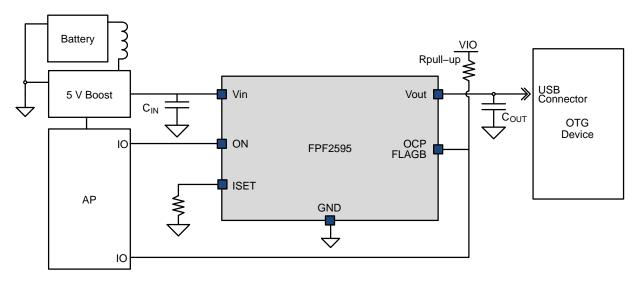
- ESD Protected:
 - ♦ Human Body Model: >2 kV
 - ◆ Charged Device Model: >1.0 kV
 - ◆ IEC61000-4-2 Air Discharge: >15 kV
 - ◆ IEC61000-4-2 Contact Discharge: >8 kV
- This is a Pb-Free Device

Applications

- Type C Power Source Switch
- Computing, Monitor
- Portable Devices

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APPLICATION DIAGRAM



NOTE:

1. C_{IN} and C_{OUT} capacitors recommended for improvement of device stability.

Figure 1. Typical Application

FUNCTIONAL BLOCK DIAGRAM

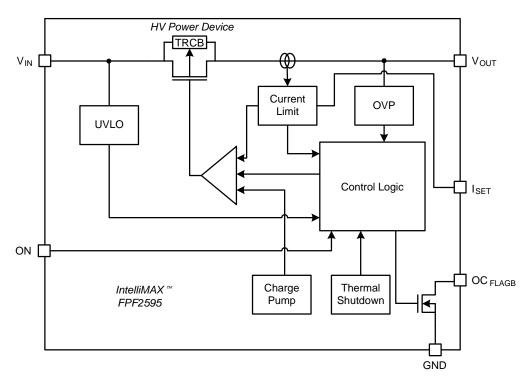


Figure 2. Functional Block Diagram

PIN CONFIGURATIONS

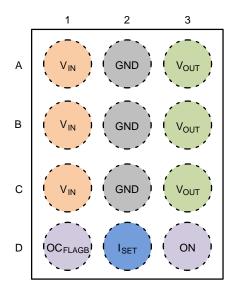


Figure 3. Pin Assignments (Top View)

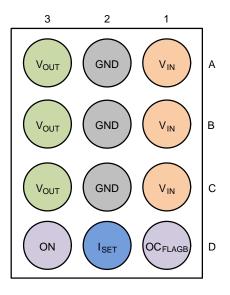


Figure 4. Pin Assignments (Bottom View)

PIN DESCRIPTION

Pin No.	Name	Description		
A3, B3, C3	V _{OUT}	Switch Output		
A1, B1, C1	V _{IN}	Supply Input: Input to the power switch		
A2, B2, C2	GND	Ground (True device ground)		
D3	ON	ON/OFF Control Input: Active HIGH – GPIO compatible Logic HIGH Switch Enable		
		Logic LOW Switch Disable		
D1	OC _{FLAGB}	Fault Output: Active LOW, open-drain output that indicates an input over current. External pull-up resistor to V _{CC} is required.		
D2	I _{SET}	Current Limit Set Input: A resistor from ISET to ground sets the current	nt limit for the switch.	

ABSOLUTE MAXIMUM RATINGS

Symbol	F	Parameter	Min	Max	Unit
V _{PIN}	V _{OUT} to GND, V _{OUT} to V _{IN}		-0.3	28.0	V
	ON, V _{IN} , FLAGB, I _{SET} to GND	-0.3	6.0		
I _{SW}	Maximum Continuous Switch Current	(Note 2)	-	3.9	Α
t _{PD}	Total Power Dissipation at T _A = 25°C		-	1.48	W
TJ	Operating Junction Temperature			+150	°C
T _{STG}	Storage Junction Temperature			+150	°C
Q_JA	Thermal Resistance, Junction-to-Ambient (1-inch Square Pad of 2 oz. Copper)			84.1 (Note 3)	°C/W
ESD	Electrostatic Discharge Capability Human Body Model, JESD22-A114		2.0	-	kV
		Charged Device Model, JESD22-C101	1.0	-	
	IEC61000–4–2 System Level Air Discharge (V _{IN} , V _{ON} , V _{OUT} to GND) Contact Discharge (V _{IN} , V _{ON} , V _{OUT} to GND)		15.0	-	
			8.0	-	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. Maximum Junction Temperature = 85°C.

- 3. Measured using 2S2P JEDEC std. PCB.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Max	Unit
V _{IN}	Supply Voltage		5.5	V
T _A	Ambient Operating Temperature	-40	85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTICS (Unless otherwise noted; $V_{IN} = 2.5$ to 5.5 V, $T_A = -40$ to $+85^{\circ}C$; typical values are at $V_{IN} = 5$ V and $T_A = 25^{\circ}C$.)

Symbol	Parameter	Condition	Min	Тур	Max	Unit
BASIC OPER	RATION			_		
V _{IN}	Input Voltage		2.5	_	5.5	V
I _{Q(OFF)}	Off Supply Current	V _{ON} = GND, V _{OUT} = Open	-	1	2	μΑ
I _{SD(OFF)}	Shutdown Current	V _{IN} = 5.5 V, V _{OUT} = 0 V, V _{ON} = GND	-	0.1	4.0	μΑ
IQ	Quiescent Current	I _{OUT} = 0 mA	-	65	100	μΑ
R _{ON}	On Resistance	V _{IN} = 5.0 V, I _{OUT} = 1 A	-	35	50	mΩ
		V _{IN} = 3.7 V, I _{OUT} = 1 A	-	40	55	1
V_{IH}	ON Input Logic HIGH Voltage	V _{IN} = 2.5 V to 5.5 V	1.15	_	_	V
V_{IL}	ON Input Logic LOW Voltage	V _{IN} = 2.5 V to 5.5 V	-	_	0.65	V
V_{IL_FLAG}	FLAGB Output Logic LOW Voltage	V _{IN} = 5 V, I _{SINK} = 10 mA	-	0.1	0.2	V
		V _{IN} = 2.5 V, I _{SINK} = 10 mA	-	0.15	0.30	
I _{FLAGB_LK}	FLAGB Output HIGH Leakage Current	V _{IN} = 5 V, Switch On	-	_	1	μΑ
I _{ON}	On Input Leakage	V _{ON} = 0 V to V _{IN}	-	_	1.0	μΑ
R _{ON_PD}	Pull-Down Resistance at ON Pin	$V_{IN} = 2.5 \sim 5.5 \text{ V}, V_{ON} = \text{HIGH}, $ $T_A = -40 \text{ to } 85^{\circ}\text{C}$	-	14	-	МΩ
VER-VOLT	AGE PROTECTION					
V _{OV_TRIP}	Output OVP Lockout	V _{OUT} Rising Threshold	5.50	5.80	6.00	V
		V _{OUT} Falling Threshold	-	5.50	_	1
OUT _{HYS}	Output OVP Hysteresis	V _{OUT} Falling Threshold	-	0.3	_	V
t _{OVP}	OVP Response Time (Note 5)	I_{OUT} = 0.5 A, C_L = 1 μ F, T_A = 25°C, V_{OUT} from 5.5 V to 6.0 V	1	-	4	μS
OVER-CURF	RENT PROTECTION		•	•	•	<u> </u>
I _{LIM}	Current Limit (Note 4)	$V_{IN} = 5 \text{ V}, R_{SET} = 2300 \Omega, V_{OUT} = 1.68 \text{ to } 5 \text{ V}$	450	500	550	mA
		$V_{IN} = 5 \text{ V}, R_{SET} = 1070 \Omega, V_{OUT} = 1.68 \text{ to 5 V}$	900	1000	1100	
V _{UVLO}	Under-Voltage Lockout	V _{IN} Increasing	_	2.4	_	V
		V _{IN} Decreasing	_	2.2	_	1
V _{UVLO_HYS}	UVLO Hysteresis		_	200	_	mV
V _{T_RCB}	RCB Protection Trip Point	V _{OUT} – V _{IN}	_	50	_	mV
V _{R_RCB}	RCB Protection Release Trip Point	V _{IN} – V _{OUT}	_	50	_	mV
V _{RCB_HYS}	RCB Hysteresis		_	100	_	mV
t _{RCB}	Default RCB Response Time	V _{IN} = 5 V, V _{ON} = High/Low	_	2	_	μS
I _{RCB}	RCB Current	V _{ON} = 0 V, V _{OUT} = 5.5 V	_	7	-	μΑ
t _{HOCP}	Hard Over–Current Response Time	Moderate Over–Current Condition, $I_{OUT} \ge I_{LIM}$, $V_{OUT} = 0$ V	-	6	-	μS
t _{OCP}	Over–Current Response Time	Moderate Over–Current Condition, $I_{OUT} \ge I_{LIM} V_{OUT} \le V_{IN}$	-	7	-	μs
t _{OC_FLAG}	Over–Current Flag Response Time	When Over–Current Occurs to Flag Pulling LOW	-	8	-	ms
TSD	Thermal Shutdown (Note 5)	Shutdown Threshold	_	150	-	°C
		Return from Shutdown	_	130	-	1
		Hysteresis	_	20	_	1

ELECTRICAL CHARACTERISTICS (Unless otherwise noted; $V_{IN} = 2.5$ to 5.5 V, $T_A = -40$ to +85°C; typical values are at $V_{IN} = 5$ V and $T_A = 25^{\circ}C$.) (continued)

Symbol	Parameter	Condition	Min	Тур	Max	Unit	
DYNAMIC C	DYNAMIC CHARACTERISTICS						
t _{DON}	Turn-On Delay (Note 5, 6)	$V_{IN} = 5 \text{ V}, \text{ R}_{L} = 100 \Omega, \text{ C}_{L} = 1 \mu\text{F},$	_	0.69	_	ms	
t _R	V _{OUT} Rise Time (Note 5, 6)	$T_A = 25^{\circ}C, R_{SET} = 2040 \Omega$	_	0.77	_	ms	
t _{ON}	Turn-On Time (Note 5, 7)		_	1.46	_	ms	
t _{DOFF}	Turn-Off Delay (Note 5, 6)		_	10	_	μs	
t _F	V _{OUT} Fall Time (Note 5, 6)		_	220	_	μs	
t _{OFF}	Turn-Off Time (Note 5, 8)		_	230	_	μS	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 4. Characterization based on 1% tolerance resistor.
- 5. This parameter is guaranteed by design and characterization; not production tested.
- 6. t_{DON}/t_{DOFF}/t_R/t_F are defined in Figure 5 below. 7. t_{ON} = t_R + t_{DON}. 8. t_{OFF} = t_F + t_{DOFF}.

TIMING DIAGRAM

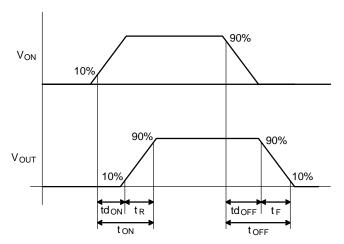


Figure 5. Timing Diagram

where:

t_{DOFF} = Delay Off Time $t_F = V_{OUT}$ Fall Time $t_{OFF} = Turn Off Time$

OPERATION AND APPLICATION DESCRIPTION

Input Capacitor

To limit the voltage drop on the input supply caused by transient inrush current when the switch turns on into discharge load capacitor; a capacitor must be placed in between the $V_{\rm IN}$ and GND pins. A high-value capacitor on CIN can be used to reduce the voltage drop in high-current applications.

Output Capacitor

An output capacitor should be placed between the V_{OUT} and GND pins. This capacitor prevents parasitic board inductance from forcing V_{OUT} below GND when the switch is on. This capacitor also prevents reverse inrush current from creating a voltage spike that could damage the device in the case of a V_{OUT} short.

Fault Reporting

Upon the detection of an over-current, OC_FLAGB signal the fault by activating LOW.

Current Limiting

The current limit ensures that the current through the switch does not exceed the maximum set value, while not limiting the minimum value. The current at which the part's limit is adjustable through the selection of the external resistor connected to the ISET pin. Information for selecting the resistor is found in the section below. The device acts as a constant—current source when the load draws more than the maximum value set by the device until thermal shutdown occurs. The device recovers if the die temperature drops below the threshold temperature.

Under-Voltage Lockout (UVLO)

The under-voltage lockout turns the switch off if the input voltage drops below the lockout threshold. With the ON pin active, the input voltage rising above the UVLO threshold releases the lockout and enables the switch.

True Reverse-Current Blocking

The true reverse-current blocking feature protects the input source against current flow from output to input regardless of whether the load switch is on or off.

Thermal Shutdown

The thermal shutdown protects the die from internally or externally generated excessive temperature. During an over-temperature condition, the switch is turned off. The switch automatically turns on again if the temperature of the die drops below the threshold temperature.

Setting Current Limit

The current limit is set with an external resistor connected between the I_{SET} and GND pins. The resistor is selected using Table 1. Resistor tolerance of 1% or less is recommended.

Table 1. CURRENT LIMIT SETTINGS BY R_{SET} (Note)

1461 (1166)					
$R_SET\Omega$	Min. Current Limit (mA)	Typ. Current Limit (mA)	Max. Current Limit (mA)		
290	3150	3500	3850		
315	2925	3250	3575		
340	2700	3000	3300		
375	2475	2750	3025		
415	2250	2500	2750		
460	2025	2250	2475		
520	1800	2000	2200		
600	1570	1750	1920		
700	1350	1500	1650		
850	1125	1250	1375		
1070	900	1000	1100		
1200	810	900	990		
1350	720	800	880		
1550	630	700	770		
1850	540	600	660		
2300	450	500	550		
2500	405	450	495		
2800	360	400	440		
3200	315	350	385		
3800	270	300	330		
4600	225	250	275		
5900	180	200	220		
7800	135	150	165		
11900	90	100	110		

9. Table values based on 1% tolerance resistor.

Current limit threshold equation (I_{LIM}):

$$\begin{split} R_{SET} \left(\Omega \right) &= \left(\frac{798439 \text{ mV}}{I_{SET} \text{ mA}} \right)^{1.044} \\ \text{Or:} &\qquad \qquad \text{(eq. 1)} \\ I_{SET} \left(\text{mA} \right) &= \frac{798439 \text{ mV}}{R_{SET}^{0.956} \Omega} \end{split}$$

If current limit is not used it is OK for the ISET pin to be connected with GND, but the maximum current must be less than the maximum current capability of 3.9 A.

BOARD LAYOUT

For best performance, all traces should be as short as possible. To be most effective, the input and output capacitors should be placed close to the device to minimize the effect that parasitic trace inductance may have on normal and short–circuit operation. Using wide traces for VIN, VOUT, GND helps minimize parasitic electrical effects along with minimizing the case—to—ambient thermal impedance.

ORDERING INFORMATION

Part Number	Top Mark	Operating Temperature Range	Package Type	Shipping [†]
FPF2595UCX	TY	−40 to 85°C	12-Ball, WLCSP, 3x4 Array, 0.4 mm Pitch, 250 μm Ball, Wafer-Level Chip-Scale Package (WLCSP) (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

The table below pertains to the Marketing outline drawing on the following page.

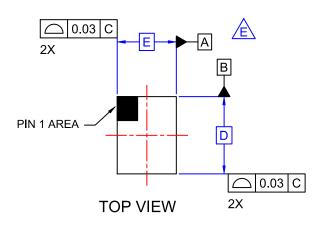
PRODUCT-SPECIFIC DIMENSIONS

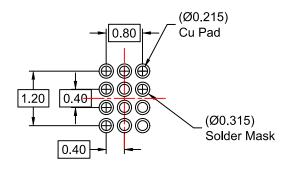
Parts	D	E	Х	Υ
FPF2595UCX	1800 μm ±30 μm	1300 μm ±30 μm	250 μm	300 μm

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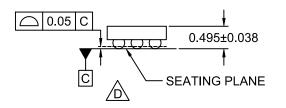
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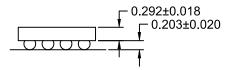
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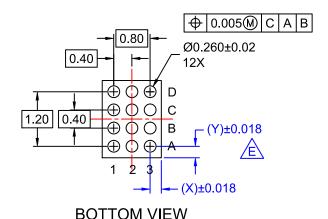


RECOMMENDED LAND PATTERN (NSMD PAD TYPE)





SIDE VIEWS



NOTES:

- A. NO JEDEC REGISTRATION APPLIES.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.

D\DATUM C IS DEFINED BY THE SPHERICAL CROWNS OF THE BALLS.

 $^\prime$ E $_{\cdot}$ FOR DIMENSIONS D, E, X, AND Y SEE PRODUCT DATASHEET.

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DESCRIPTION: WLCSP12 1.3x1.8x0.495 **PAGE 1 OF 1**

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